

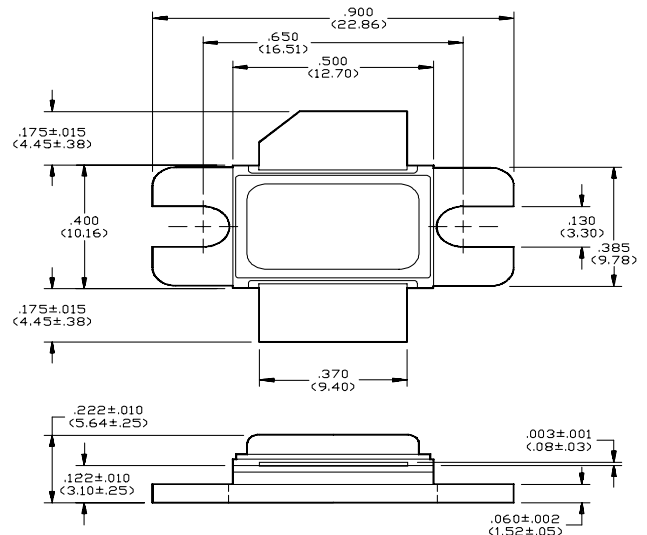
Avionics Pulsed Power Transistor - 350 Watts, 1030-1090 MHz, 250 μ s Pulse, 10% Duty



Features

- NPN Silicon Microwave Power Transistor
- Common Base Configuration
- Broadband Class C Operation
- High Efficiency Interdigitated Geometry
- Diffused Emitter Ballasting Resistors
- Gold Metalization System
- Internal Input and Output Impedance Matching
- Hermetic Metal/Ceramic Package

Outline Drawing¹

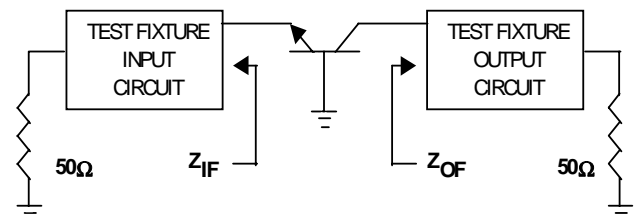


Notes: (unless otherwise specified)

1. Tolerances are: inches \pm .005" (millimeters \pm 0.13mm)

Narrowband Test Fixture Impedance

F (MHz)	Z _{IF} (Ω)	Z _{OF} (Ω)
1090	2.5 - j1.5	1.1 + j0.9



Absolute Maximum Rating at 25°C

Parameter	Symbol	Rating	Units
Collector-Emitter Voltage	V _{CES}	80	V
Emitter-Base Voltage	V _{EBO}	3.0	V
Collector Current (Peak)	I _C	17	A
Total Power Dissipation @ +25°C	P _{TOT}	750	W
Storage Temperature	T _{stg}	-65 to +200	°C
Junction Temperature	T _j	200	°C

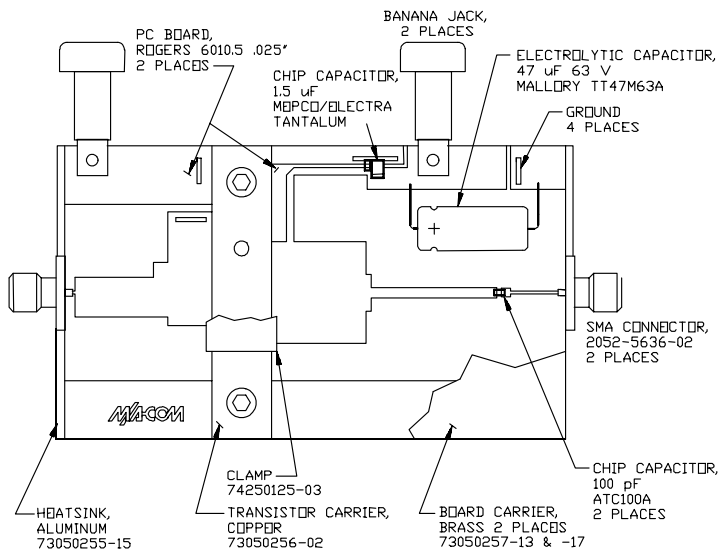
Electrical Specifications at 25°C

Symbol	Parameter	Test Conditions	Min	Max	Units
BV _{CES}	Collector-Emitter Breakdown	I _C =250mA	80	-	V
I _{CES}	Collector-Emitter Leakage	V _{CE} =45 V	-	25	mA
R _{TH(JC)}	Thermal Resistance	V _{CC} =45 V, P _{in} =350 W, f=1090 MHz	-	0.2	°C/W
P _{in}	Input Power	V _{CC} =45 V, P _{in} =350 W, f=1090 MHz	-	55	W
G _P	Power Gain	V _{CC} =45 V, P _{in} =350 W, f=1090 MHz	8.0	-	dB
η	Collector Efficiency	V _{CC} =45 V, P _{in} =350 W, f=1090 MHz	55	-	%
R _L	Input Return Loss	V _{CC} =45 V, P _{in} =350 W, f=1090 MHz	9	-	dB
VSWR-T	Load Mismatch Tolerance	V _{CC} =45 V, P _{in} =350 W, f=1090 MHz	-	2:1	-
VSWR-S	Load Mismatch Stability	V _{CC} =45 V, P _{in} =350 W, f=1090 MHz	-	1.5:1	-

V2.00

Test Fixture Electrical Schematic

Top View



Circuit Dimensions

